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correct
a first conductive layer formed on said gate insulating film;

a second conductive layer electrically connected to said first conductive layer; and

an insulating film comprising oxide of said first and second conductive layers,

wherein said first conductive layer comprises a first material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt,

wherein said second conductive layer comprises a second material which is different from said first material,

wherein a width of said first conductive layer is narrower than that of said second conductive layer, and

wherein said insulating film is formed on at least side surfaces of said first and second conductive layers.

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15. (Amended) A semiconductor device according to claim 11, wherein said semiconductor layer comprises a pair of impurity regions in said semiconductor layer with a channel region interposed therebetween.

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16. (Amended) A semiconductor device comprising:

a semiconductor layer;

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a gate insulating film formed on said semiconductor layer;

a first conductive layer formed on said gate insulating film;

a second conductive layer electrically connected to said first conductive layer wherein said first conductive layer comprises a different material from said first conductive layer; and

an insulating film comprising oxide of said first and second conductive layers,

wherein said first conductive layer comprises a first material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt,

wherein said second conductive layer comprises a second material which is different from said first material,

wherein a width of said first conductive layer is narrower than that of said second conductive layer, and

wherein said insulating film is formed on side surfaces of said first and second conductive layers and a top surface of said second conductive layer.

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20. (Amended) A semiconductor device according to claim 11, wherein said semiconductor layer comprises a pair of impurity

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regions in said semiconductor layer with a channel region
interposed therebetween.

21. (Amended) A semiconductor device comprising:

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a gate electrode comprising a first conductive layer
formed on an insulating surface and a second conductive layer
formed on said first conductive layer;

an insulating film formed on said gate electrode;

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a semiconductor layer comprising a source region, a
drain region, and a channel region formed on said insulating
film,

wherein said first conductive layer comprises a first
material selected from the group consisting of molybdenum,
tantalum, aluminum, chromium, nickel, zirconium, titanium,
palladium, silver, copper, and cobalt,

wherein said second conductive layer comprises a
second material which is different from said first material, and

wherein a width of said second conductive layer is
narrower than that of said first conductive layer.

25. (Amended) A semiconductor device comprising:

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a gate electrode comprising a first conductive layer
formed on an insulating surface and a second conductive layer
formed on said first conductive layer;

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a gate insulating film formed on said gate electrode;
a semiconductor layer comprising a source region, a
drain region, and a channel region formed on said insulating
film, and

an insulating film comprising oxide of said first and
second conductive layers,

wherein said first conductive layer comprises a first
material selected from the group consisting of molybdenum,
tantalum, aluminum, chromium, nickel, zirconium, titanium,
palladium, silver, copper, and cobalt,

wherein said second conductive layer comprises a
second material which is different from said first material, and

wherein a width of said second conductive layer is
narrower than that of said first conductive layer, and

wherein said insulating film is formed on at least
side surfaces of said first and second conductive layers.
